

Fall 10-4-2015

Combining in situ tensile testing and orientation microscopy in the SEM: A MEMS based setup for studying time dependent deformation of thin films by TKD and STEM

Jan Philipp Liebig

Materials Science & Engineering, Institute I, FAU Erlangen-Nürnberg, jan.p.liebig@fau.de

Benoit Merle

Materials Science & Engineering, Institute I, FAU Erlangen-Nürnberg

Mathias Goken

Materials Science & Engineering, Institute I, FAU Erlangen-Nürnberg

Follow this and additional works at: http://dc.engconfintl.org/nanomechtest_v



Part of the [Materials Science and Engineering Commons](#)

Recommended Citation

[1] R.R. Keller, R.H. Geiss, J. Microsc. 245 (2012) 245. [2] P.W. Trimby et al., Acta Mater. 62 (2014) 69. [3] E. Hosseinian, O.N. Pierron, Nanoscale 5 (2013) 12532.

This Abstract is brought to you for free and open access by the Proceedings at ECI Digital Archives. It has been accepted for inclusion in Nanomechanical Testing in Materials Research and Development V by an authorized administrator of ECI Digital Archives. For more information, please contact franco@bepress.com.

COMBINING IN SITU TENSILE TESTING AND ORIENTATION MICROSCOPY IN THE SEM: A MEMS BASED SETUP FOR STUDYING TIME DEPENDENT DEFORMATION OF THIN FILMS BY TKD AND STEM

Jan Philipp Liebig, Materials Science & Engineering, Institute I, FAU Erlangen-Nürnberg, Germany
jan.p.liebig@fau.de

Benoit Merle, Materials Science & Engineering, Institute I, FAU Erlangen-Nürnberg, Germany
Mathias Göken, Materials Science & Engineering, Institute I, FAU Erlangen-Nürnberg, Germany

Key Words: In situ testing, TKD, MEMS, Thin films

Structures in integrated devices are constantly subjected to residual or thermal stresses during operation. Understanding the relaxation behavior of thin films is therefore critical for improving their reliability. Recently it was shown that Transmission Kikuchi Diffraction (TKD) in the Scanning Electron Microscope (SEM) enables the determination of local crystal orientations with high spatial resolution using standard Electron Backscatter Diffraction (EBSD) instrumentation [1, 2]. Giving access to quantitative information on mechanisms like grain growth, grain rotation and strain gradient evolution, time resolved TKD stands out as a promising technique for the characterization of microstructural changes upon relaxation of thin films. We have implemented a MEMS based tensile device [3] into a custom setup specifically designed for in situ TKD imaging inside the SEM. A scanning TEM detector is used complementarily to access shorter time scales. In this context, a novel technique for the preparation and mounting of freestanding thin film tensile samples is presented, which relies on focused ion beam (FIB) milling and selective, electron-beam-assisted etching of silicon membranes. First stress relaxation results of tests on fcc metallic thin films are shown to demonstrate the capabilities of time resolved TKD.

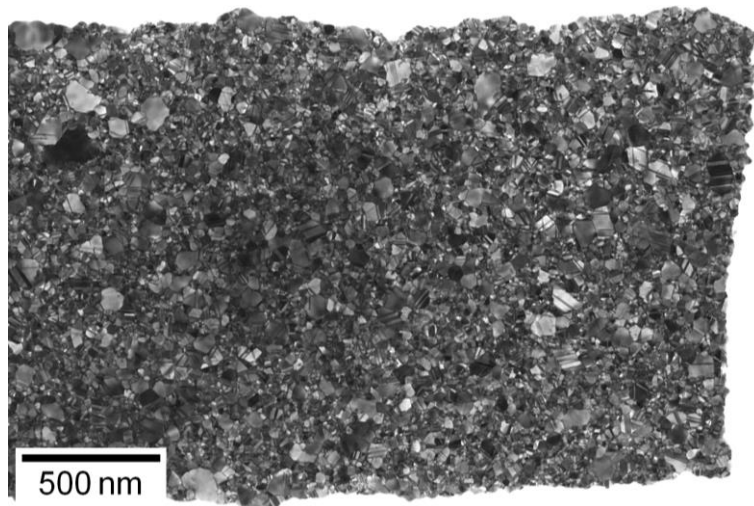


Figure 1 – STEM micrograph of a 30 nm thick gold specimen after fracture

- [1] R.R. Keller, R.H. Geiss, J. Microsc. 245 (2012) 245.
- [2] P.W. Trimby et al., Acta Mater. 62 (2014) 69.
- [3] E. Hosseinian, O.N. Pierron, Nanoscale 5 (2013) 12532.